

TQTHL3124V5

Single-Line ESD Protection Array

Description

The TQTHL3124V5 Series is designed with AF technology to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium.

It has been specifically designed to protect sensitive components which are connected to data and transmission lines from over voltage caused by ESD(electrostatic discharge), and EFT (electrical fast transients).

• Feature

- Single-channel ESD protection
- Peak Power Dissipation-1800W(8*20us Waveform)
- Replacement for MLV
- Protects I/O Port
- Low Clamping Voltage
- Low Leakage
- Response Time is <1ns</p>
- RoHS Compliant
- Meets MSL 1 Requirements
- Reliable silicon device avalanche breakdown Structure

	Symbol	Parameter			
•	ElectronicaParametering Voltage				
	I _R	Reverse Leakage Current @			
		V _{RWM}			
	V _{BR}	Breakdown Voltage @ I _T			
	IT	Test Current			
	Ipp	Maximum Reverse Peak Pulse			
		Current			
	Vc	Clamping Voltage @ IPP			

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PIN configuration



DFN1610-2L

• Applications

- > Cell phone handsets and accessories
- Personal Digital Assistants
- Portable Instrumentation
- Digital Cameras
- Power supply protection
- Other electronics equipments communication systems

Protection solution to meet

- IEC61000-4-2(ESD) ±30Kv(contact), ±30kV(air)
- IEC61000-4-5 (Surge) 170A(8/20us)





Absolute maximum rating @TA=25°C •

Symbol	Parameter	Value	Units
ESD	ESD Rating per IEC61000-4-2:Contact	30	K)/
	Air	30	ΓV
P _{PPP}	Peak Pulse Power (8/20µS)	2300	W
T _{STG}	Storage Temperature	-55/+150	°C
TJ	Operating Temperature	-55/+125	°C

Electrical Characteristics @TA=25°C

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working	V _{RWM}	Any I/O to Ground			4.5	V
Voltage						
	N	lt = 1mA		5.0		N
Breakdown Voltage	VBR	Any I/O to Ground		5.3		V
Reverse Leakage Current	I _R	VRWM =12V, T=25°C			1	μA
Clamping Voltage	V _{C1}	IPP =100A, tP = 8/20µs		9.1		V
Clamping Voltage	V _{C2}	IPP=60A, tP = 8/20µs		11.3		V
Junction Consoitance	0	VR = 0V, f = 1MHz,		450		ъĘ
Junction Capacitance	CJ	any I/O pin to Ground		450		pr
Peak pulse current	I _{pp}	Any I/O to Ground			170	A
Deals Dulas Dewer	D	Peak Pulse Power			2200	14/
reak ruise Power	P PPP	(8/20µS)			2300	vv

Typical Performance Characteristics •









Pulse Waveform



Power Derating Curve

• Solder Reflow Recommendation

Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec

Non-Repetitive Peak Pulse Power vs. Pulse Time



TQTHL3124V5



• Package Information

Ordering Information

Device	Marking	Package	Qty per Reel	Reel Size
TQTHL3124V5	4.5H	DFN1610-2L	10000	7 Inch

Mechanical Data

Case: DFN1610-2L

Case Material: Molded Plastic. UL Flammability



	COMMON DIME	NSION (MM)		
PKG	DFN1610			
REF.	MIN.	NDM.	MAX	
A	0.45	0.50	0.55	
D	1.55	1.60	1.65	
E	0.95	1.00	1.05	
b	0.35	0.40	0.45	
L	0.75	0.80	0.85	
e	1.10BSC			
h	0.15	0.20	0.25	

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